

Abstract

In a method for producing an SOI wafer comprising steps of implanting hydrogen ions etc. from a ~~surface of a bond wafer 21~~ surface to form an ion-implanted layer 24 inside the wafer, bonding the ion-implanted bond wafer surface of the bond wafer and a surface of a base wafer 22 via an oxide film 23 or directly, and forming an SOI wafer by delaminating by heat treatment a part of the bond wafer at the ion-implanted layer ~~by heat treatment, wherein the bond wafer is a silicon wafer consisting that consists of a silicon~~ single crystal grown by ~~Cheehralski-Czochralski~~ Czochralski method, ~~which that~~ is occupied by N region outside OSF generated in a ring shape and that has no defect region detected by Cu deposition method, ~~is used as the bond wafer. Thereby, even in the case of forming an extremely thin SOI layer 27 such that, for example, its having a thickness is of 200 nm or less, there is provided~~ can provide an SOI wafer ~~which that~~ has an excellent electric property without ~~causing~~ micro pits caused by acid cleaning with hydrofluoric acid etc., and ~~in addition,~~ can be produced without increasing the number of ~~process~~ processes.